



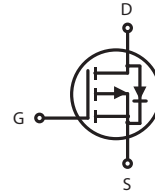
P-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
-30V	-20A	32 @ V _{GS} = -10V
		55 @ V _{GS} = -4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- TO-252 and TO-251 Package.

ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous @ T _C =25°C -Pulsed ^a	I _D	-20	A
	I _{DM}	-60	A
Drain-Source Diode Forward Current	I _S	-20	A
Maximum Power Dissipation @ T _C =25°C	P _D	50	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 175	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	R _{θJC}	3	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	50	°C/W

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ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-25			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V			-1	uA
Gate-Body Leakage	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS^a						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.7	-3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-20A		27	32	m ohm
		V _{GS} =-4.5V, I _D =-10A		41	55	m ohm
On-State Drain Current	I _{D(ON)}	V _{DS} =-10V, V _{GS} =-10V	-30			A
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-10A		14		S
DYNAMIC CHARACTERISTICS^b						
Input Capacitance	C _{ISS}	V _{DS} =-15V, V _{GS} =0V f=1.0MHz		950		pF
Output Capacitance	C _{OSS}			250		pF
Reverse Transfer Capacitance	C _{RSS}			170		pF
Gate resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1.0MHz		2.6		ohm
SWITCHING CHARACTERISTICS^b						
Turn-On Delay Time	t _{D(ON)}	V _{DD} =-15V I _D =-1 A V _{GS} =-10V R _{GEN} =6 ohm		10		ns
Rise Time	t _r			22		ns
Turn-Off Delay Time	t _{D(OFF)}			68.8		ns
Fall Time	t _f			38.5		ns
Total Gate Charge (10V)	Q _g	V _{DS} =-15V, I _D =-20A V _{GS} =-10V		18.5		nC
Total Gate Charge (4.5V)				9.6		nC
Gate-Source Charge	Q _{gs}			1.6		nC
Gate-Drain Charge	Q _{gd}			5.8		nC

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ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS ^a						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_s = -10A$		-0.9	-1.3	V

Notes

- a. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

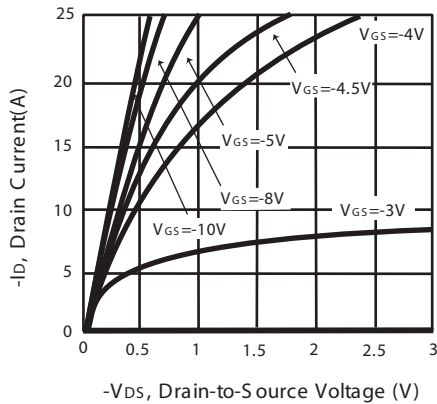


Figure 1. Output Characteristics

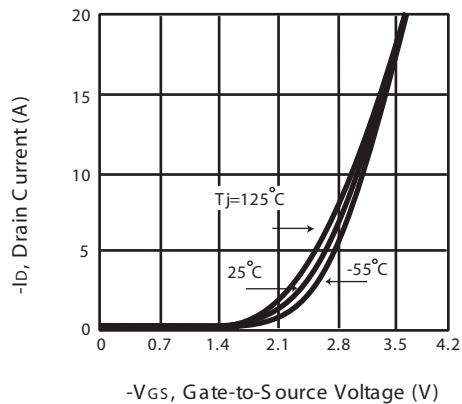


Figure 2. Transfer Characteristics

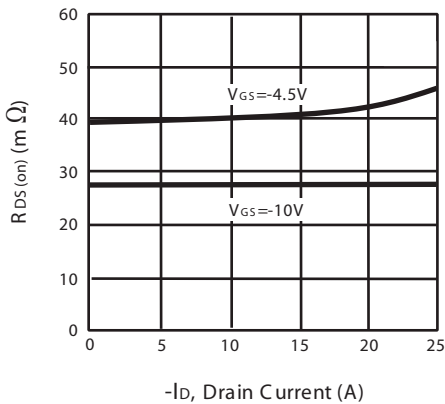


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

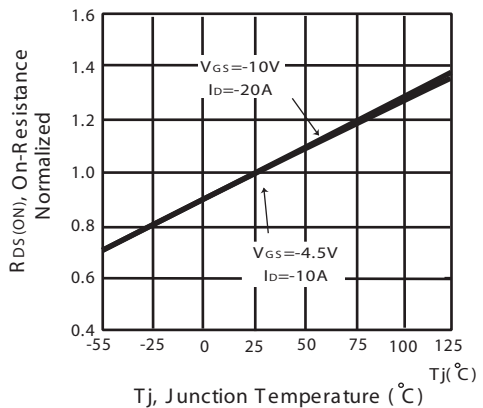


Figure 4. On-Resistance Variation with Drain Current and Temperature

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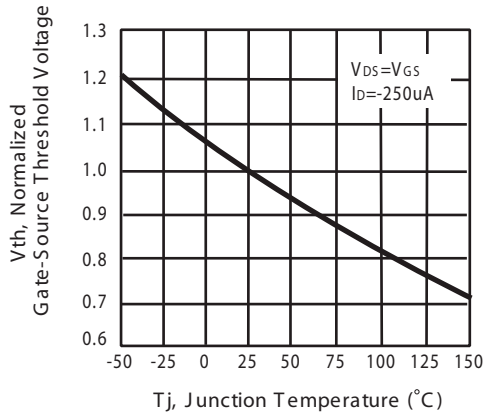


Figure 5. Gate Threshold Variation with Temperature

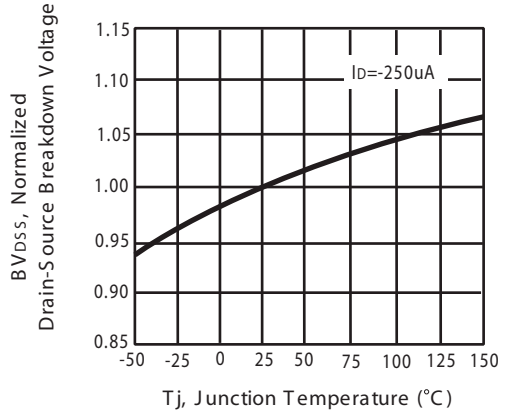


Figure 6. Breakdown Voltage Variation with Temperature

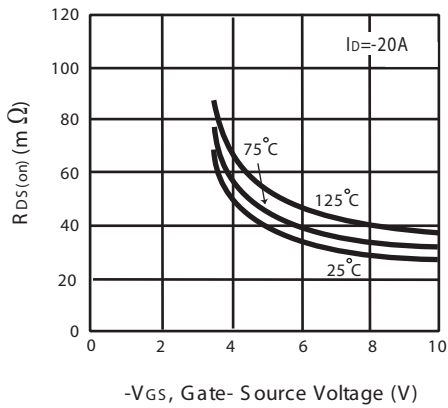


Figure 7. On-Resistance vs. Gate-Source Voltage

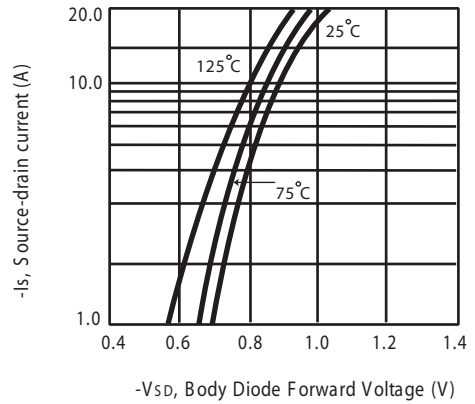


Figure 8. Body Diode Forward Voltage Variation with Source Current

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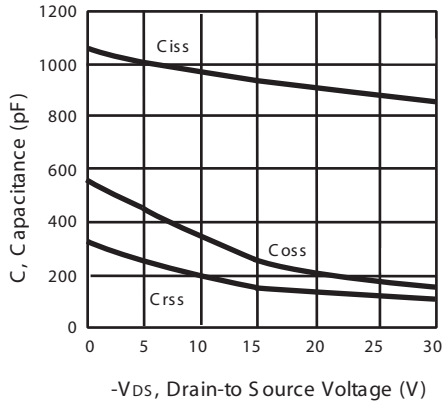


Figure 9. Capacitance

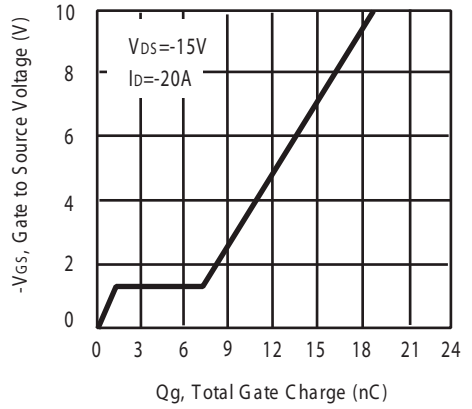


Figure 10. Gate Charge

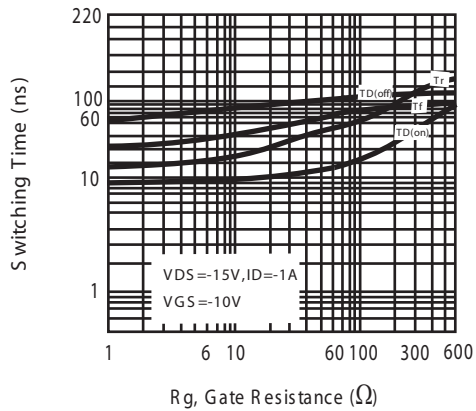


Figure 11. switching characteristics

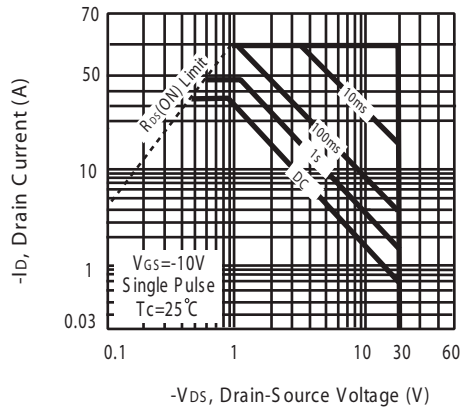


Figure 10. Maximum Safe Operating Area

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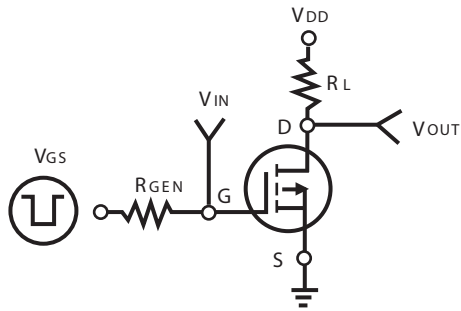


Figure 11. Switching Test Circuit

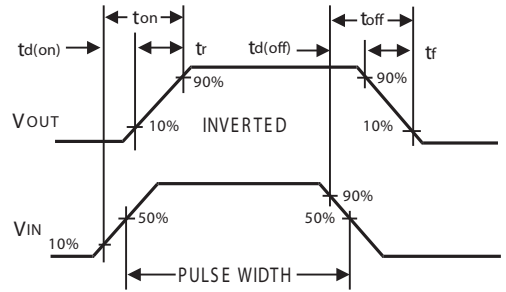


Figure 12. Switching Waveforms

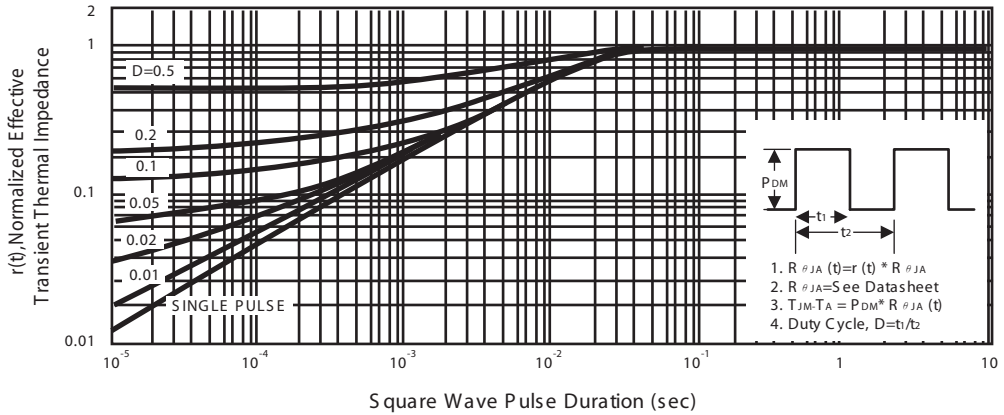
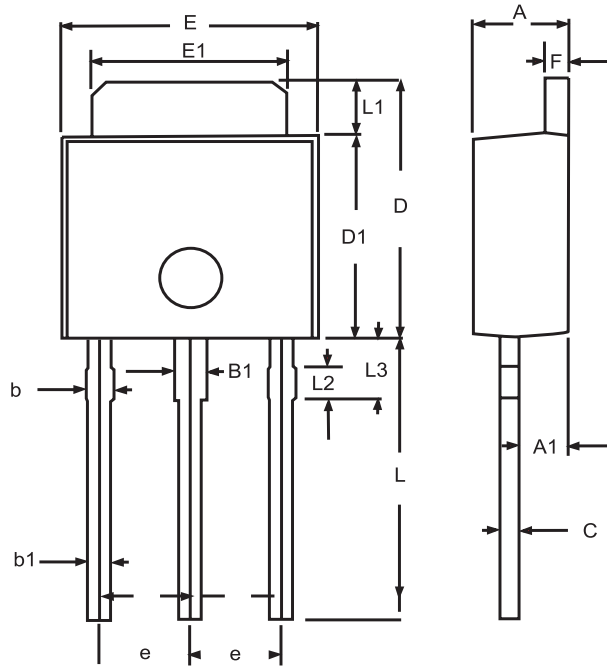


Figure 13. Normalized Thermal Transient Impedance Curve

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PACKAGE OUTLINE DIMENSIONS

TO-251

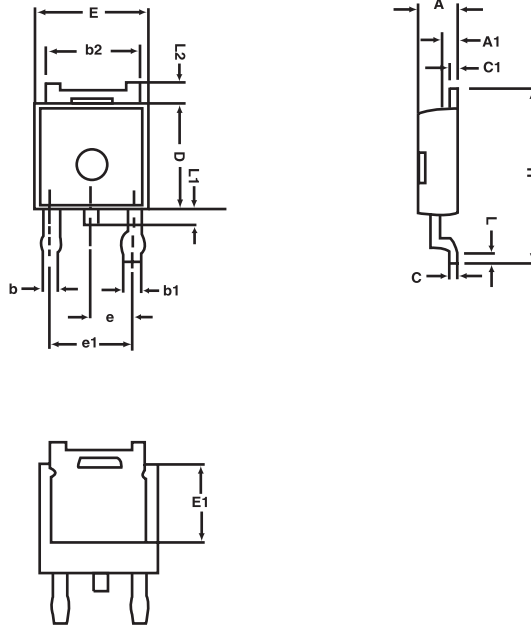


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.20	2.40	0.087	0.095
A1	1.100	1.300	0.043	0.051
B1	0.650	1.050	0.026	0.041
b	0.500	0.900	0.020	0.035
b1	0.400	0.800	0.016	0.32
C	0.400	0.600	0.016	0.024
D	6.700	7.300	0.264	0.287
D1	5.400	5.650	0.213	0.222
E	6.40	6.650	0.252	0.262
e	2.100	2.500	0.083	0.098
F	0.400	0.600	0.016	0.024
L	7.000	8.000	0.276	0.315
L1	1.300	1.700	0.051	0.067
L2	0.700	0.900	0.028	0.035
L3	1.400	1.800	0.055	0.071

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PACKAGE OUTLINE DIMENSIONS

TO-252

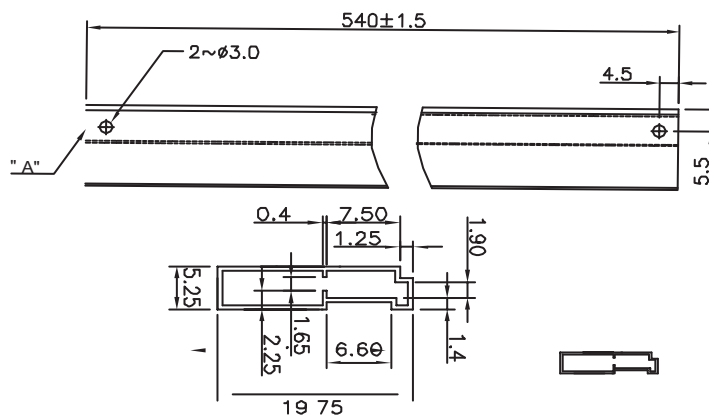


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.25	2.35	0.089	0.093
A1	0.95	1.05	0.037	0.041
b	0.77	0.85	0.030	0.033
b1	0.84	0.94	0.033	0.037
b2	5.30	5.45	0.209	0.215
C	0.49	0.53	0.019	0.021
D	6.00	6.20	0.236	0.244
E	6.40	6.60	0.252	0.260
E1	3.18	3.67	0.125	0.145
e	2.29	BSC	0.090	BSC
H	9.70	10.10	0.382	0.398
L	1.425	1.625	0.056	0.064
L1	0.650	0.850	0.026	0.033
L2	0.600	REF.	0.024	REF.

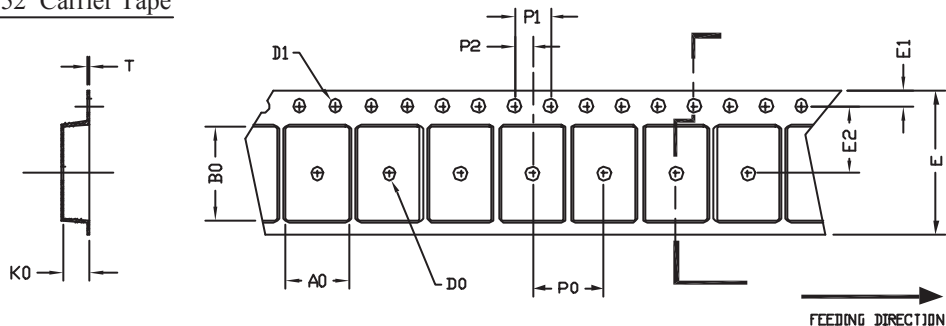
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TO251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



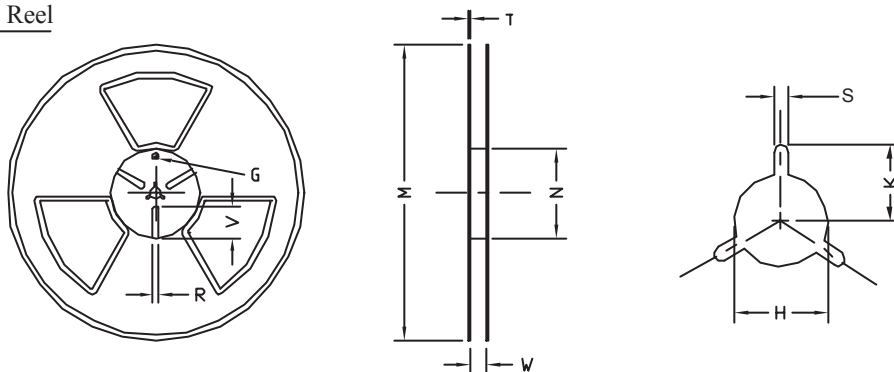
TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.80 ± 0.1	10.3 ± 0.1	2.50 ± 0.1	$\phi 2$	$\phi 1.5$ $+ 0.1$ $- 0$	16.0 $0.3 \pm$	1.75 $0.1 \pm$	7.5 ± 0.15	8.0 ± 0.1	4.0 ± 0.1	2.0 ± 0.15	0.3 ± 0.05

TO-252 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	$\phi 330$	$\phi 330$ ± 0.5	$\phi 97$ ± 1.0	17.0 $+ 1.5$ $- 0$	2.2	$\phi 13.0$ $+ 0.5$ $- 0.2$	10.6	2.0 ± 0.5	---	---	---